

WHAT IS CLAIMED IS:

1. A material for purification of a semiconductor polishing slurry which is used to remove metals present in  
5 the semiconductor polishing slurry, comprising:
  - a functional group capable of forming a metal chelate;
  - a fibrous substrate of which at least the surface is fixed onto by the functional group.
- 10 2. A material for purification of a semiconductor polishing slurry which is used to remove metals present in the semiconductor polishing slurry, comprising:
  - a functional group capable of ion-exchanging with a hydroxyl group or capable of forming a metal chelate;
  - 15 a fibrous substrate of which at least the surface is fixed onto by the functional group.
3. A material for purification of a semiconductor polishing slurry according to claim 2,
  - wherein the hydroxyl group is an ethylenical hydroxyl group and fixed onto the surface of the fibrous substrate in  
20 a hydroxyl value of 40 mg KOH/g or more.
4. A material for purification of a semiconductor polishing slurry according to any of claims 1 to 3,
  - wherein the fibrous substrate is at least one selected from a plant-based natural fiber, an animal-based natural  
25 fiber, a cellulose-based regenerated fiber and a polyvinyl alcohol-based synthetic polymer fiber.
5. A material for purification of a semiconductor polishing slurry according to any of claims 1 to 4, which is

used to remove metals present in the semiconductor polishing slurry,

wherein the functional group capable of forming a metal chelate is at least one group selected from a group containing aminocarboxylic acids, a group containing phosphoric acids, a group containing thio compounds and a group with at least a part of acid type functional groups of these groups determined as alkali metal salt or ammonium salt.

6. A material for purification of a semiconductor polishing slurry, which is used to remove metals present in the semiconductor polishing slurry according to any of claims 1 to 5,

wherein the functional group capable of forming a metal chelate is a group containing amines or hydroxylamines.

7. A material for purification of a semiconductor polishing slurry used to remove metals present in the semiconductor polishing slurry,

wherein two or more of the materials for purification of the semiconductor polishing slurry having a different substrate and/or functional group among the materials for purification of a semiconductor polishing slurry according to any of claims 1 to 6 are laminated to form a layer or mixed.

8. A material for purification of a semiconductor polishing slurry used to remove metals present in the semiconductor polishing slurry,

wherein the material for purification of a semiconductor polishing slurry according to any of claims 1 to 6 is formed

into a self-supportable sheet or felt.

9. A module for purification of a semiconductor polishing slurry,

wherein the material for purification of a semiconductor polishing slurry according to any of claims 1 to 8 is charged in a container provided with an inflow port and an outflow port for the polishing slurry so as to allow the polishing slurry to flow through it.

10. A module for purification of a semiconductor polishing slurry,

wherein the material for purification of a polishing slurry according to any of claims 1 to 8 is disposed in a flowable state within an area partitioned by a filter or a strainer through which the polishing slurry flows in a container provided with an inflow port and an outflow port for the semiconductor polishing slurry.

11. A process for purification of a semiconductor polishing slurry, comprising:

passing an object semiconductor polishing slurry through at least one of the material for purification of a semiconductor polishing slurry according to claims 1 to 8 or the module for purification of a semiconductor polishing slurry according to claims 9 and 10 to remove metals present in the object semiconductor polishing slurry;

supplying all of the object semiconductor polishing slurry to a step of polishing a semiconductor after removing the metals present in it; or

after introducing at least a part or all of it to the

original semiconductor polishing slurry and circulating again,  
supplying any of them to the step of polishing semiconductor.

12. A process for purification of a semiconductor  
polishing slurry according to claim 11,

5 wherein when a semiconductor polishing slurry being  
purified is acidic, an acid type end group of a functional  
group capable of forming a metal chelate is determined as an  
acid type (H type), and

when the polishing slurry being purified is alkaline, an  
10 acid type end group of a functional group capable of forming  
a metal chelate is determined as alkali metal salt or  
ammonium salt, and the object semiconductor polishing slurry  
is passed through at least one of the material for  
purification of a semiconductor polishing slurry according to  
15 any of claims 1 to 8 or the module for purification of a  
semiconductor polishing slurry according to claims 9 and 10  
to remove metals present in the object semiconductor  
polishing slurry.

13. A process for purification of a semiconductor  
20 polishing slurry according to claim 11 or 12,

wherein when the object semiconductor polishing slurry  
is alkaline, the acid type end group of the functional group  
capable of forming the metal chelate is determined as alkali  
metal salt or ammonium salt which is a main component showing  
25 alkalinity of the object semiconductor polishing slurry.

14. A process for purification of a semiconductor  
polishing slurry according to any one of claims 11 to 13,

wherein pH of the semiconductor polishing slurry is

adjusted before purification to decrease a change in the pH of the purified semiconductor polishing slurry.